

JB99 is high reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

### Features

- High speed switching
- High Current
- High surge resistivity for CRT discharge
- High reliability design
- High Voltage

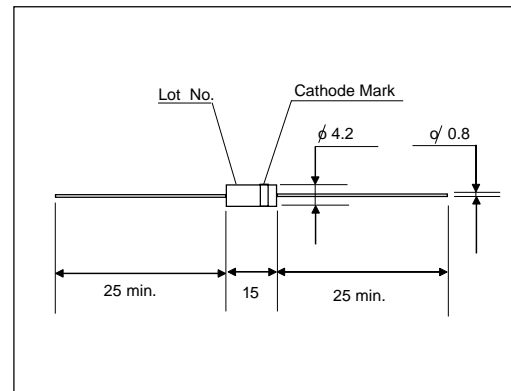
### Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

### Maximum Ratings and Characteristics

- Absolute Maximum Ratings

### Outline Drawings : mm



### Cathode Mark

Type	Mark
JB99	

Items	Symbols	Condition	JB99	Units
Repetitive Peak Reverse Voltage	$V_{RRM}$		20	kV
Average Output Current	$I_o$	Ta=25°C, Resistive Load	20	$mA_{peak}$
Surge Current	$I_{FSM}$		1.0	$A_{peak}$
Junction Temperature	$T_j$		155	°C
Allowable Operation Case Temperature	$T_c$		120	°C
Storage Temperature	$T_{stg}$		-40 to +155	°C

- Electrical Characteristics (Ta=25°C Unless otherwise specified)

Items	Symbols	Conditions	JB99T	Units
Maximum Forward Voltage Drop	$V_F$	at 25°C, $I_F = I_{F(AV)}$	40	V
Maximum Reverse Current	IR1	at 25°C, $V_R = V_{RRM}$	3.0	$\mu A$
	IR2	at 100°C, $V_R = V_{RRM}$	30	$\mu A$
Maximum Reverse Recovery Time	$T_{rr}$	at 25°C	100	nS
Junction Capacitance	$C_j$	at 25°C, $V_R = 0V, f = 1MHz$	1.0	pF